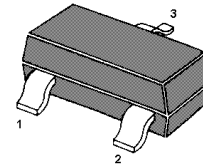


MMBT8550 (2A)

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into two groups C and D according to its DC current gain.



1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	40	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	25	V
Emitter Base Voltage	$-V_{\text{EBO}}$	6	V
Collector Current	$-I_{\text{C}}$	2	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 5\text{ mA}$	h_{FE}	45	-	-
at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 100\text{ mA}$	h_{FE}	100	250	-
	h_{FE}	160	300	-
at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 1.5\text{ A}$	h_{FE}	40	-	-
Collector Base Cutoff Current				
at $-V_{\text{CB}} = 35\text{ V}$	$-I_{\text{CBO}}$	-	100	nA
Emitter Base Cutoff Current				
at $-V_{\text{EB}} = 6\text{ V}$	$-I_{\text{EBO}}$	-	100	nA
Collector Base Breakdown Voltage				
at $-I_{\text{C}} = 100\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{CBO}}$	40	-	V
Collector Emitter Breakdown Voltage				
at $-I_{\text{C}} = 2\text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	25	-	V
Emitter Base Breakdown Voltage				
at $-I_{\text{E}} = 100\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{EBO}}$	6	-	V
Collector Emitter Saturation Voltage				
at $-I_{\text{C}} = 1.5\text{ A}$, $-I_{\text{B}} = 100\text{ mA}$	$-V_{\text{CE}(\text{sat})}$	-	0.5	V
Base Emitter Saturation Voltage				
at $-I_{\text{C}} = 1.5\text{ A}$, $-I_{\text{B}} = 100\text{ mA}$	$-V_{\text{BE}(\text{sat})}$	-	1.2	V
Base Emitter Voltage				
at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 10\text{ mA}$	$-V_{\text{BE}(\text{on})}$	-	1	V
Transition Frequency				
at $-V_{\text{CE}} = 10\text{ V}$, $-I_{\text{C}} = 50\text{ mA}$	f_{T}	100	-	MHz

